

Silicon NPN Power Transistors

2SC3886A

DESCRIPTION

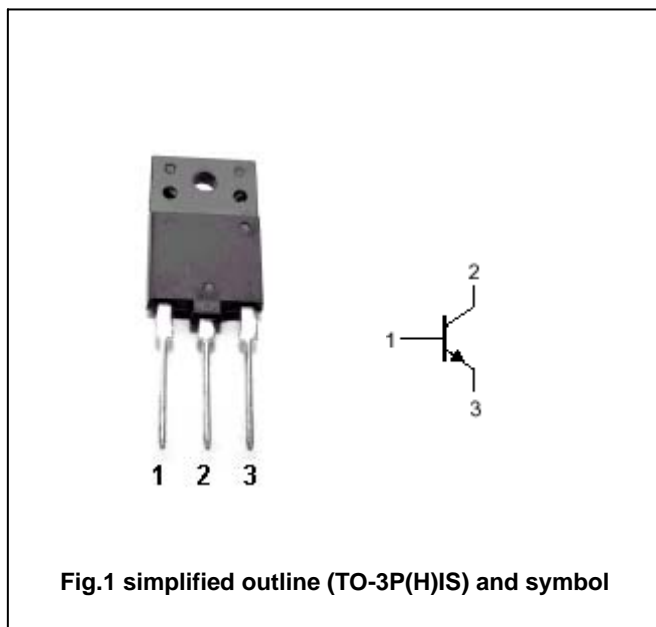
- With TO-3P(H)IS package
- High voltage ,high speed

APPLICATIONS

- Horizontal deflection output for high resolution display
- High speed switching regulator output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		15	A
I_B	Base current		4	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ; I _B =0	600			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A ; I _B =1.5A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A ; I _B =1.5A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1500V; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μ A
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	8	15		
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V	1	3		MHz
C _{OB}	Collector output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		210		pF
t _s	Storage time	Resistive load I _{CP} =6A ; I _{B1} =-I _{B2} =1.2A R _L =33.3 Ω			2.5	μ s
t _f	Fall time				0.15	μ s

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PACKAGE OUTLINE

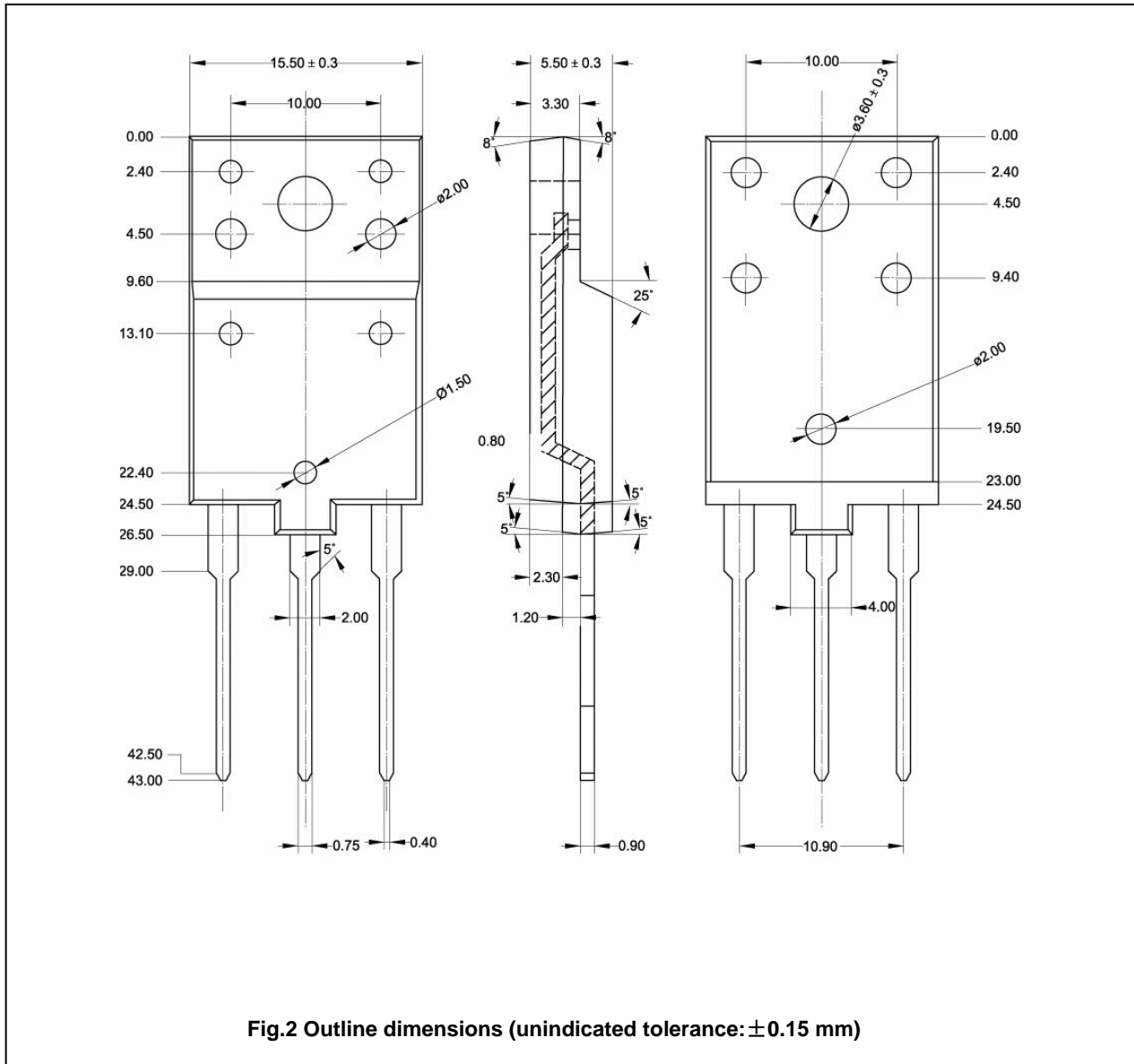


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)